

SEMICONDUCTOR TECHNICAL DATA

KTD1413

EPITAXIAL PLANAR NPN TRANSISTOR

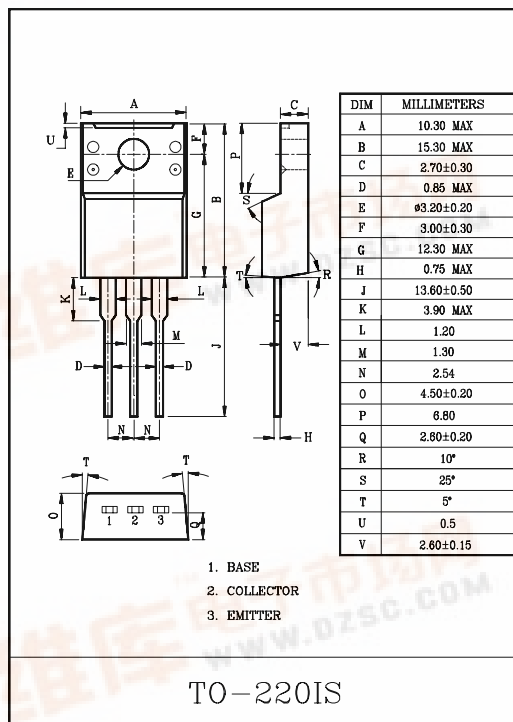
HIGH POWER SWITCHING APPLICATIONS.
HAMMER DRIVER, PULSE MOTOR DRIVER APPLICATIONS.

FEATURES

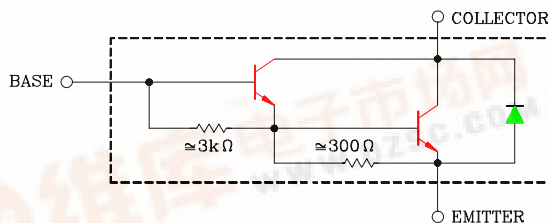
- High DC Current Gain : $h_{FE}=2000$ (Min.) at $V_{CE}=2V$, $I_C=3A$.
- Low Saturation Voltage : $V_{CE(sat)}=1.5V$ (Max.) at $I_C=3A$.

MAXIMUM RATINGS (Ta=25°C)

CHARACTERISTIC	SYMBOL	RATING	UNIT
Collector-Base Voltage	V_{CBO}	150	V
Collector-Emitter Voltage	V_{CEO}	100	V
Emitter-Base Voltage	V_{EBO}	7	V
Collector Current	I_C	5	A
Base Current	I_B	0.5	A
Collector Power Dissipation (Tc=25°C)	P_C	25	W
Junction Temperature	T_j	150	°C
Storage Temperature Range	T_{stg}	-55 ~ 150	°C



EQUIVALENT CIRCUIT



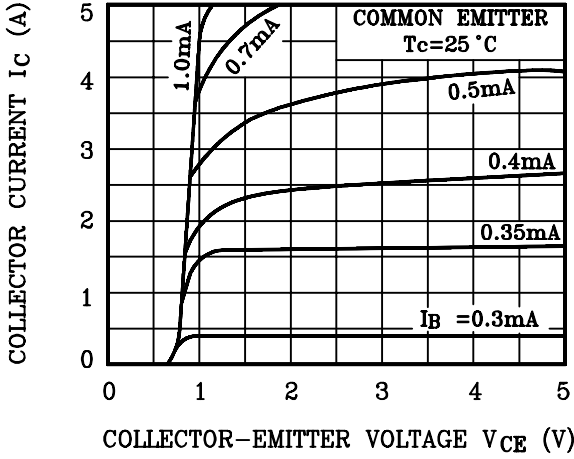
ELECTRICAL CHARACTERISTICS (Ta=25°C)

CHARACTERISTIC	SYMBOL	TEST CONDITION	MIN.	TYP.	MAX.	UNIT	
Collector Cut-off Current	I_{CBO}	$V_{CB}=100V$, $I_E=0$	-	-	1	mA	
Collector-Emitter Breakdown Voltage	$V_{(BR)CEO}$	$I_C=10mA$, $I_B=0$	100	-	-	V	
DC Current Gain	$h_{FE}(1)$	$V_{CE}=2V$, $I_C=3A$	2000	6000	15000		
	$h_{FE}(2)$	$V_{CE}=2V$, $I_C=5A$	500	-	-		
Saturation Voltage	Collector-Emitter	$V_{CE(sat)}$	$I_C=3A$, $I_B=3mA$	-	0.9	1.5	V
	Base-Emitter	$V_{BE(sat)}$	$I_C=3A$, $I_B=3mA$	-	1.6	2.0	
Switching Time	Turn-on Time	t_{on}		-	1.0	-	μS
	Storage Time	t_{stg}		-	3.5	-	
	Fall Time	t_f		-	1.2	-	

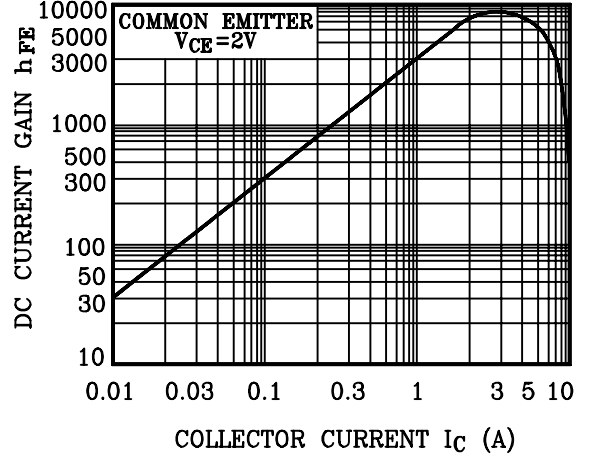
$I_{B1} = -I_{B2} = 3mA$
 $V_{CC} = 50V$
 DUTY CYCLE $\leq 1\%$

KTD1413

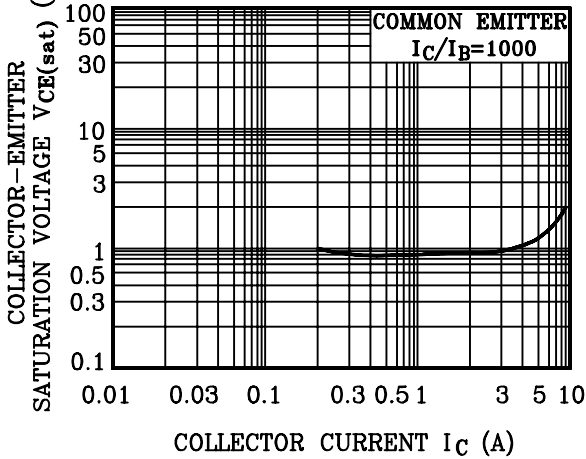
$I_C - V_{CE}$



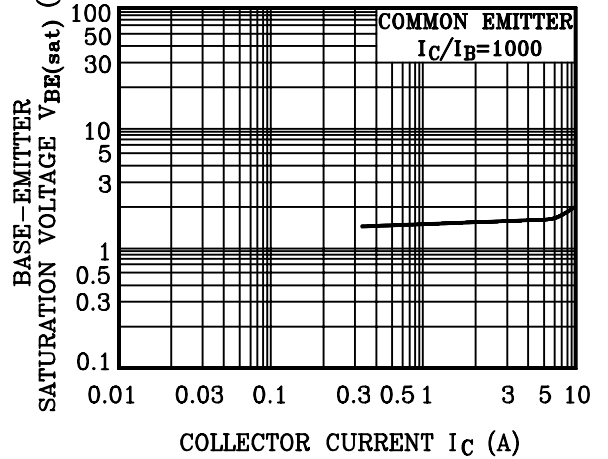
$h_{FE} - I_C$



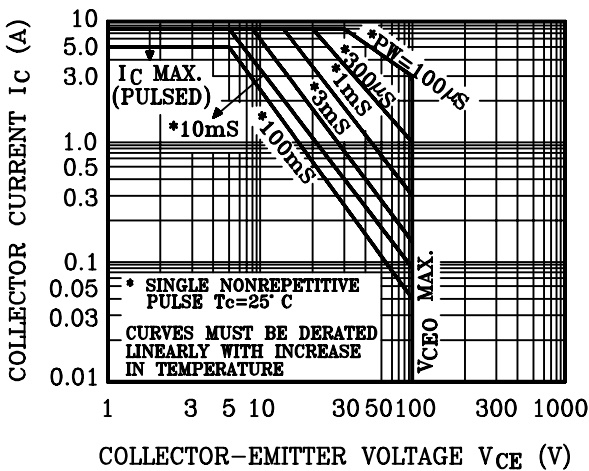
$V_{CE(sat)} - I_C$



$V_{BE(sat)} - I_C$



SAFE OPERATING AREA



$P_C - T_a$

